

CLAIMS

1. An embedded resistor comprising a thin film cermet material deposited by sputtering on a substrate and having a nearly zero TCR, said thin film cermet material comprising $M_xSi_yO_z$,
5 where $M = W$ or Ta
2. The invention according to claim 1 wherein deposition onto the substrate is performed by sputtering of a composite target of W , or Ta , and SiO_2 .
3. The invention according to claim 1 wherein deposition onto the substrate is performed by co-sputtering of two targets: a first target of W or Ta and a second target of SiO_2 .
4. The invention according to claim 2 wherein said substrate is copper foil.
5. The invention according to claim 3 wherein said substrate is copper foil.
6. The invention according to claim 2 wherein said thin film cermet material is deposited by r.f. sputtering on a substrate.
7. The invention according to claim 3 wherein sputtering of said SiO_2 target is r.f. sputtering.
8. A method for forming a cermet thin film resistor such as the one described in claim 6 including the steps of:
depositing said thin film resistor on a substrate utilizing r.f. magnetron sputtering with argon gas; and,

controlling the resistivity and TCR of said cermet thin film resistor by varying the sputtering power and pressure.

9. A method for forming a cermet thin film resistor such as the one described in claim 7, which includes the steps of: deposition of the film on a substrate utilizing r.f. and d.c. magnetron sputtering with argon gas; and controlling the resistivity and TCR of the cermet thin film by varying the sputtering power and pressure.
10. The method according to claim 8 wherein the resistor film is approximately 1000 angstroms thick and the substrate comprises an oxidized silicon substrate; the method including the further steps of controlling sputtering power and pressure to obtain Rs and TCR values in accordance with the following table:

Rs (ohms/Square)	TCR (ppm/C)	Pressure (mTorr)	Power (kW)
250	≤ -200	10	2.0
400	≤ -220	14	1.0
800	≤ -260	14	0.4
1500	≤ -400	18	0.4